

IN THE SPECIFICATION:

Please replace paragraph [0051] with the following:

[0051] FIG. 8A illustrates the results of removal of reduced island 52. Reduced island 52 is preferably removed with an etch that is selective to isolation film 36 and spacer 28, leaving an isolation structure 48 that extends into and above isolation trench 32, forming a nail shaped structure having a head 54 extending above and away from isolation trench 32 upon an oxide layer 44. The future or current active area of semiconductor substrate 12, which may be at least partially covered over by head 54, is substantially prevented from a detrimental charge and current leakage by head 54. For example, etching may be performed using an etch recipe that etches the isolation film 36 and spacer 28 faster than the isolation structure 48 by a ratio in a range of from about 1:1 to about 2:1, more specifically, by a ratio of about 1.3:1 to about 1.7:1.